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STPS10SM80C

Power Schottky rectifier

Features

- High junction temperature capability
- Optimized trade-off between leakage current and forward voltage drop
- Low leakage current
- Avalanche capability specified
- Insulated package TO-220FPAB
  - insulated voltage: 2000 V
  - package capacitance: 45 pF

Description

This dual diode Schottky rectifier is suited for high frequency switch mode power supply.

Packaged in TO-220AB, I²PAK, D²PAK and TO-220FPAB, this device is particularly suited for use in notebook, game station, LCD TV and desktop adapters, providing these applications with a good efficiency at both low and high load.

Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	2 x 5 A
V_{RRM}	80 V
T_j (max)	175 °C
V_F (typ)	485 mV

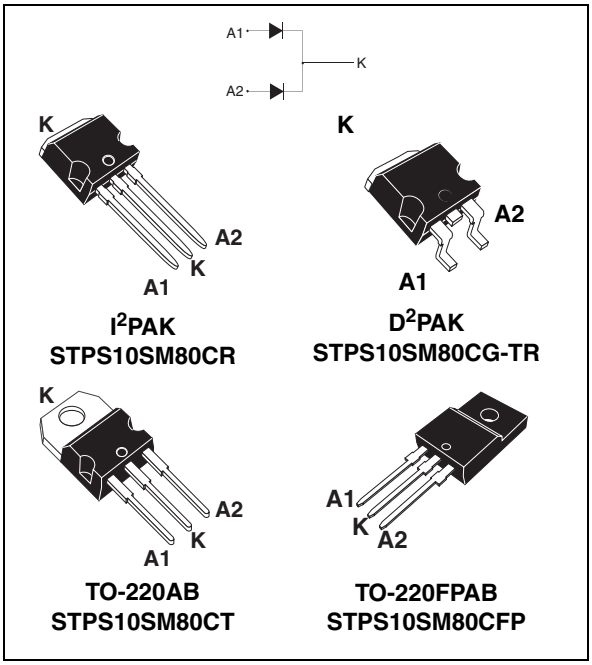
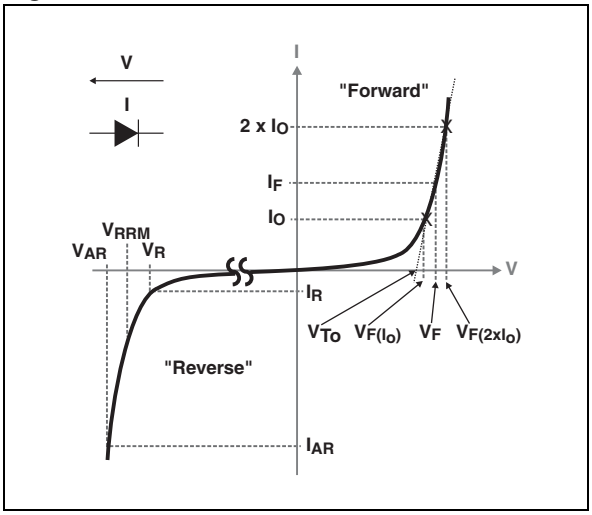


Figure 1. Electrical characteristics(a)



a. V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in *Figure 13*. V_{AR} and I_{AR} are pulse measurements (t_p < 1 µs). V_R, I_R, V_{RRM} and V_F, are static characteristics

1 Characteristics

Table 2. Absolute ratings (limiting values, per diode, at T_{amb} = 25 °C unless otherwise specified)

Symbol	Parameter				Value	Unit
V_{RRM}	Repetitive peak reverse voltage				80	V
$I_{F(RMS)}$	Forward rms current				30	A
$I_{F(AV)}$	Average forward current, δ = 0.5	TO-220AB, I^2PAK, D^2PAK	T_c = 160 °C T_c = 160 °C	Per diode Per device	5 10	A
		TO-220FPAB	T_c = 150 °C T_c = 140 °C	Per diode Per device	5 10	
I_{FSM}	Surge non repetitive forward current	t_p = 10 ms sinusoidal		T_c = 25 °C	150	A
P_{ARM}(1)	Repetitive peak avalanche power		T_j = 25 °C, t_p = 1 µs		3200	W
V_{ARM}(2)	Maximum repetitive peak avalanche voltage	t_p < 1 µs, T_j < 150 °C, I_{AR} < 9.6 A			100	V
V_{ASM}(2)	Maximum single pulse peak avalanche voltage	t_p < 1 µs, T_j < 150 °C, I_{AR} < 9.6 A			100	V
T_{stg}	Storage temperature range				-65 to +175	°C
T_j	Maximum operating junction temperature(3)				175	°C

1. For temperature or pulse time duration deratings, please refer to figure 3 and 4. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.
2. See *Figure 13*
3. $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal parameters

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AB I^2PAK, D^2PAK	per diode	3.20	°C/W
			total	1.95	
		TO-220FPAB	per diode	6.10	
			total	4.85	
$R_{th(c)}$	Coupling	TO-220AB I^2PAK, D^2PAK		0.70	°C/W
		TO-220FPAB		3.60	

When the two diodes 1 and 2 are used simultaneously:

ΔT_j(diode 1) = P(diode 1) x $R_{th(j-c)}$(Per diode) + P(diode 2) x $R_{th(c)}$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
I_R(1)	Reverse leakage current	T_j = 25 °C	$V_R = V_{RRM}$	-	3.2	15	µA
		T_j = 125 °C		-	2.8	8	mA
V_F(2)	Forward voltage drop	T_j = 25 °C	I_F = 2.5 A	-	0.560	0.610	V
		T_j = 125 °C		-	0.485	0.520	
		T_j = 25 °C	I_F = 5 A	-	0.685	0.745	
		T_j = 125 °C		-	0.575	0.615	
		T_j = 25 °C	I_F = 10 A	-	0.815	0.880	
		T_j = 125 °C		-	0.660	0.730	

1. Pulse test: t_p = 5 ms, δ < 2 %
2. Pulse test: t_p = 380 µs, δ < 2 %

To evaluate the conduction losses use the following equation:
$P = 0.50 \times I_{F(AV)} + 0.023 \times I_F{}^2{}_{(RMS)}$

Figure 2. Average forward power dissipation versus average forward current (per diode)

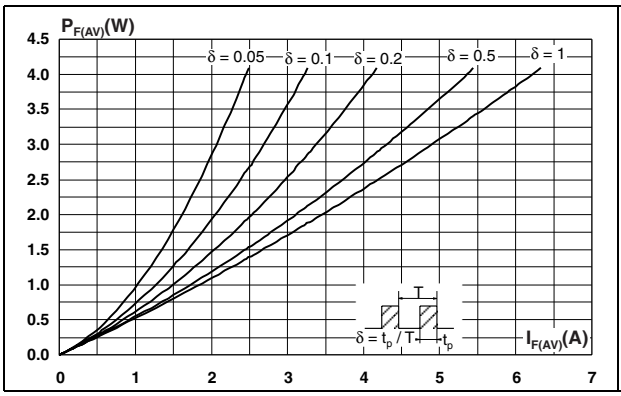


Figure 3. Average forward current versus ambient temperature (δ = 0.5, per diode)

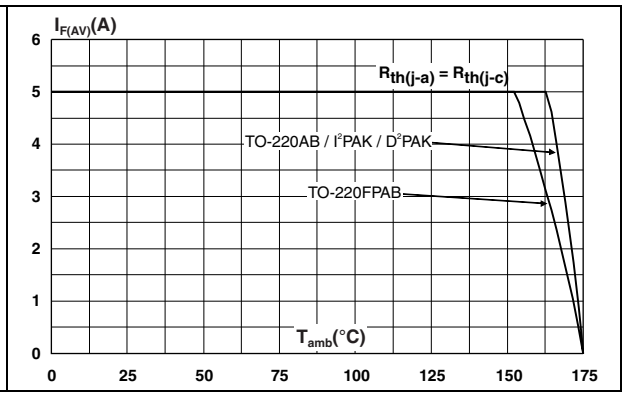


Figure 4. Normalized avalanche power derating versus pulse duration

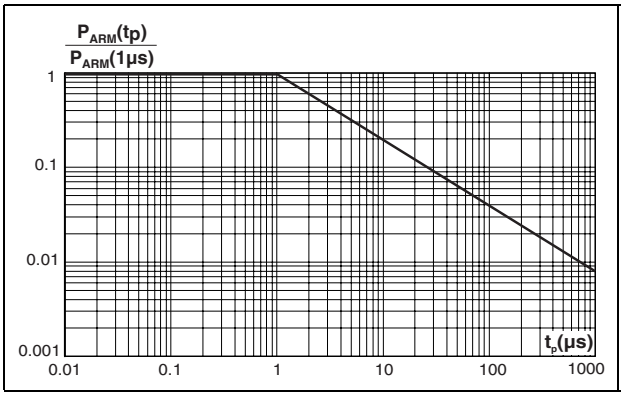


Figure 5. Normalized avalanche power derating versus junction temperature

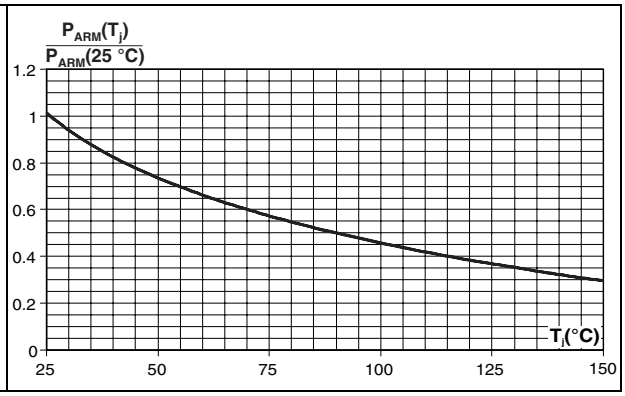


Figure 6. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

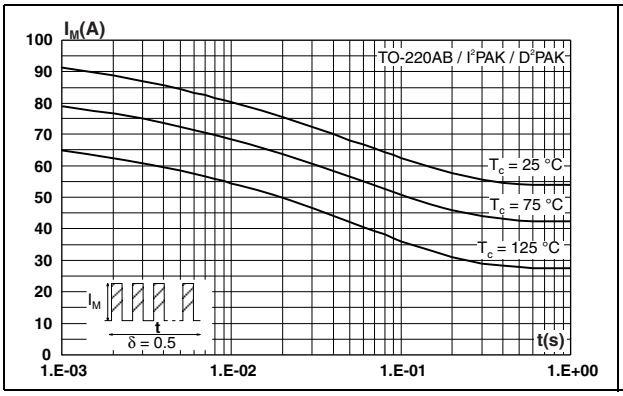


Figure 7. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

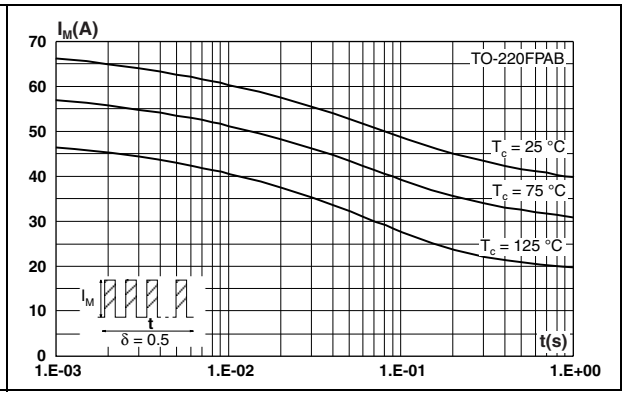


Figure 8. Relative thermal impedance junction to case versus pulse duration

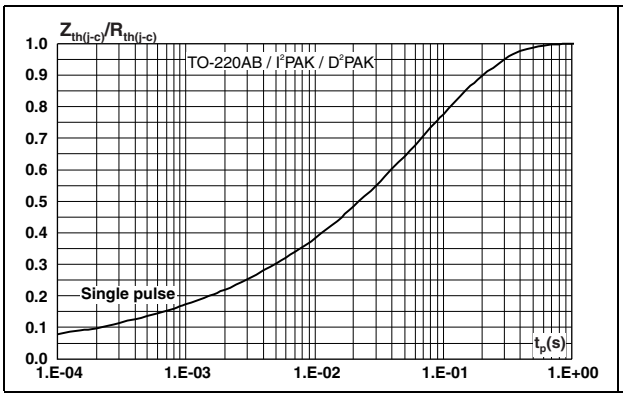


Figure 9. Relative thermal impedance junction to case versus pulse duration (TO-220FPAB)

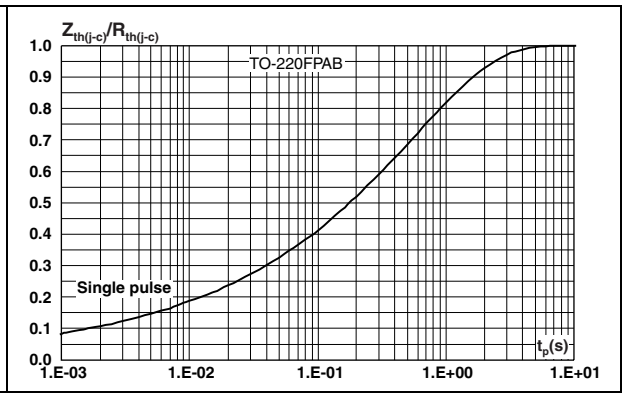


Figure 10. Reverse leakage current versus reverse voltage applied (typical values, per diode)

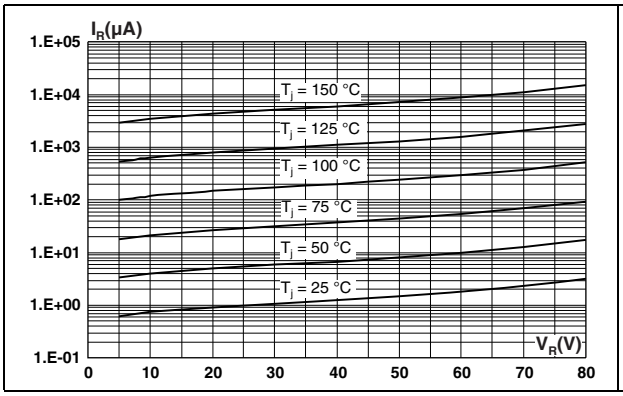


Figure 11. Junction capacitance versus reverse voltage applied (typical values, per diode)

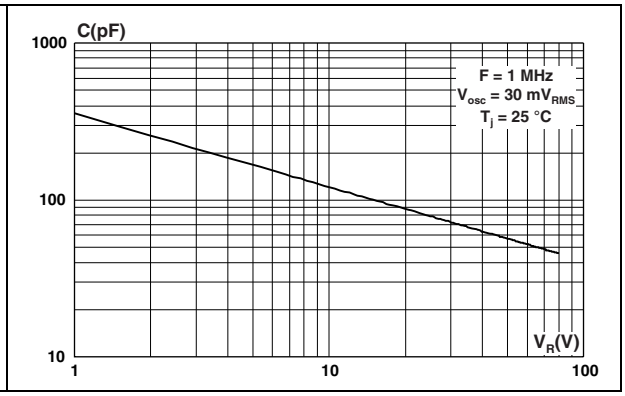


Figure 12. Forward voltage drop versus forward current (per diode)

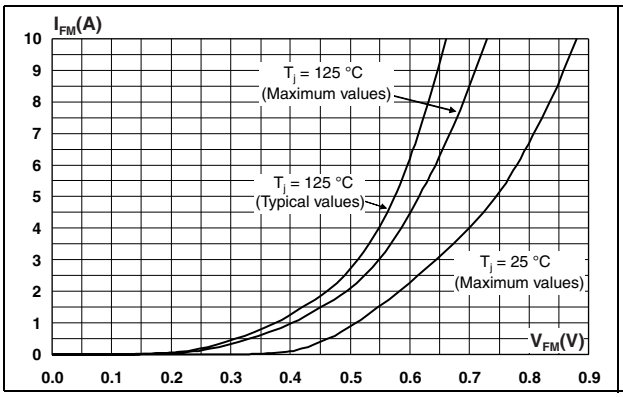


Figure 13. Reverse safe operating area (t_p < 1 µs and T_j < 150 °C)

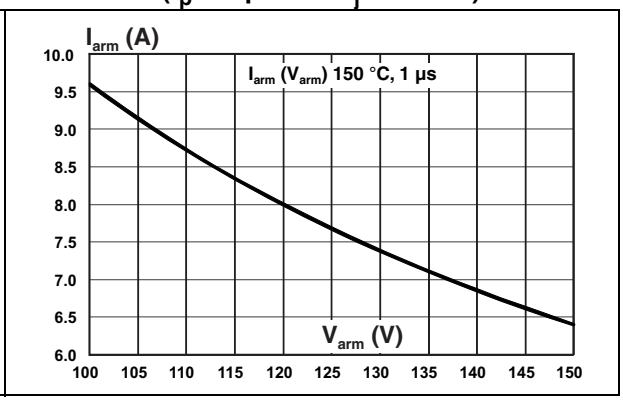
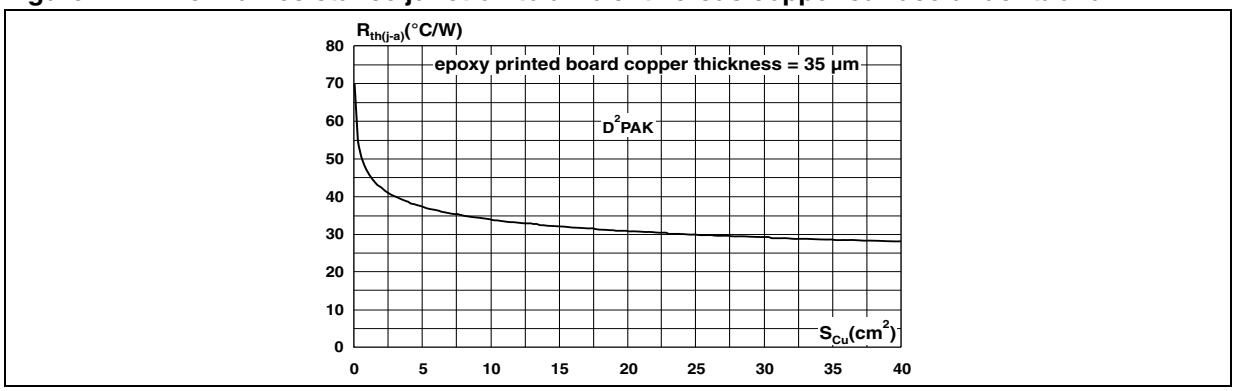


Figure 14. Thermal resistance junction to ambient versus copper surface under tab for D^2PAK

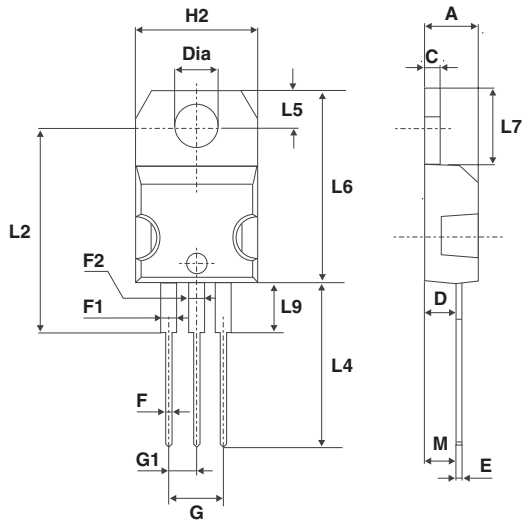


2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N·m

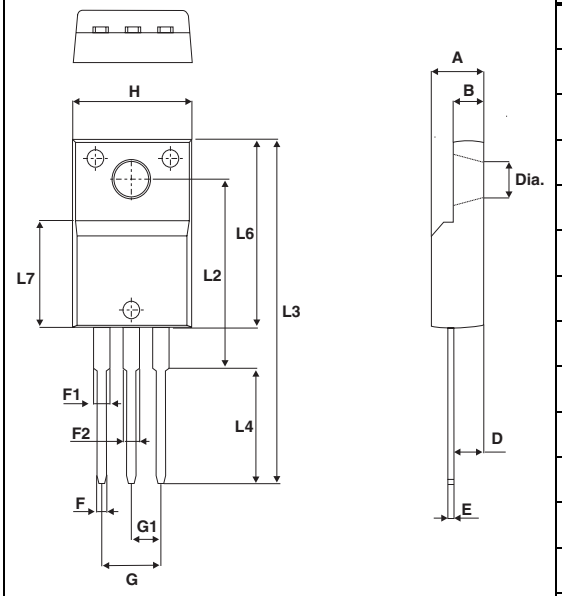
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 5. TO-220AB dimensions



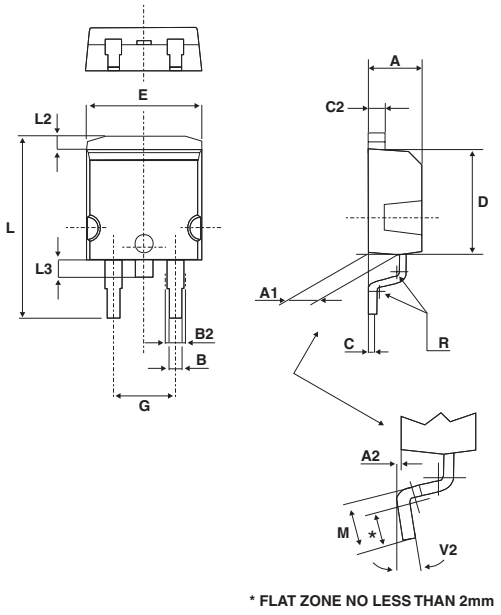
Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 Typ.		0.645 Typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 Typ.		0.102 Typ.	
Dia.	3.75	3.85	0.147	0.151

Table 6. TO-220FPAB dimensions



Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.9	0.173	0.192
B	2.5	2.9	0.098	0.114
D	2.45	2.75	0.096	0.108
E	0.4	0.7	0.016	0.028
F	0.6	1	0.024	0.039
F1	1.15	1.7	0.045	0.067
F2	1.15	1.7	0.045	0.067
G	4.95	5.2	0.195	0.205
G1	2.4	2.7	0.094	0.106
H	10	10.7	0.394	0.421
L2	16 Typ.		0.630 Typ.	
L3	28.6	30.6	1.126	1.205
L4	9.8	10.7	0.386	0.421
L6	15.8	16.4	0.622	0.646
L7	9	9.9	0.354	0.390
Dia.	2.9	3.5	0.114	0.138

Table 7. D²PAK dimensions



Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

Figure 15. D²PAK footprint (dimensions in mm)

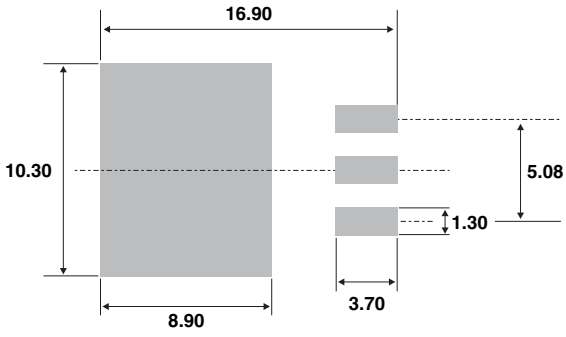
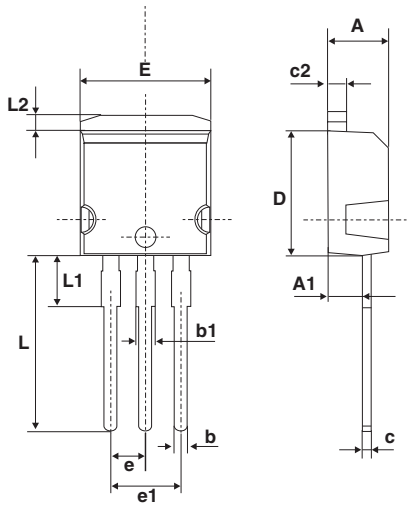


Table 8. I^2PAK dimensions



Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.40	2.72	0.094	0.107
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.044	0.067
c	0.49	0.70	0.019	0.028
c2	1.23	1.32	0.048	0.052
D	8.95	9.35	0.352	0.368
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
E	10	10.40	0.394	0.409
L	13	14	0.512	0.551
L1	3.50	3.93	0.138	0.155
L2	1.27	1.40	0.050	0.055

3 Ordering information

Table 9. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS10SM80CT	PS10SM80CT	TO-220AB	1.9 g	50	Tube
STPS10SM80CFP	PS10SM80CFP	TO-220FPAB	2.0 g	50	Tube
STPS10SM80CR	PS10SM80CR	I^2PAK	1.49 g	50	Tube
STPS10SM80CG-TR	PS10SM80CG	D^2PAK	1.48 g	1000	Tape and reel

4 Revision history

Table 10. Revision history

Date	Revision	Changes
11-Apr-2011	1	First issue.

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